Supporting Information

Anisotropic Photoresponse Behavior in Single-crystal LaAlO₃based Vacuum-ultraviolet Photodetector

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Hongxuan Wang, ^b Shi Fang, ^a Yang Kang, ^a Xin Liu, ^a Yuanmin Luo, ^a Haochen Zhang, ^a

Dongyang Luo, ^a and Haiding Sun*^a

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R. China E-mail: haiding@ustc.edu.cn

^{b.}Department of Materials Science and Engineering, Southern University of Science and Technology, Shenzhen 518055, P. R. China

^{c.}State Key Laboratory of Optoelectronic Materials and Technologies, School of Materials, Sun Yat-sen University, Guangzhou 510275, P. R. China S1. AFM images of LaAlO₃ three different crystal planes (100), (110), and (111) and their corresponding roughnesses (RMS).

Crystal	Roughness	Roughness	Roughness	Roughness	Roughness	Average
plane	of Area 1	of Area 2	of Area 3	of Area 4	of Area 5	roughness
(100)	1.08 nm	1.05 nm	1.83 nm	1.02 nm	1.54 nm	1.30 nm
(110)	1.15 nm	1.12 nm	1.09 nm	1.40 nm	0.49 nm	1.05 nm
(111)	0.98 nm	1.31 nm	1.01 nm	1.30 nm	1.27 nm	1.17 nm

Table S1. Roughness measured at different wafer positions of the three wafers

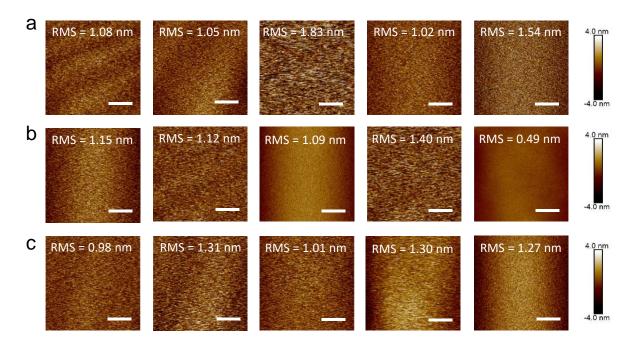


Figure S1. AFM images of three different crystal planes (a) (100), (b) (110), and (c) (111)., each of them sampled five regions (scale bar, 500 nm).

S2. Optical image and SEM image of the LaAlO₃ MSM PDs.

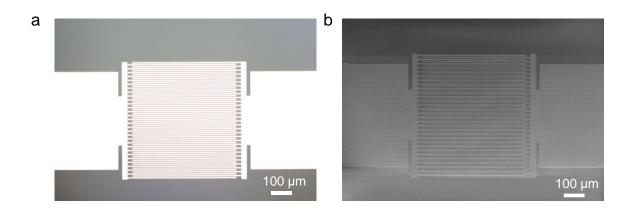


Fig.S2 (a) Optical image and (b) SEM image of interdigitated-electrode with 5 μ m finger width on LaAlO₃ single crystal.

S3. *I-V* measurements of the LaAlO₃ MSM PDs with three different crystal planes (100), (110), and (111).

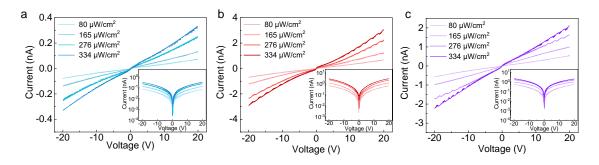


Figure S3. *I-V* characteristics of the LaAlO₃ MSM PDs with three different crystal planes (a) (100), (b) (110), and (c) (111) under 185 nm illumination with different intensities. The inset plots the *I-V* curves in the log form.

S4. *I*_{photo}-*t* measurements of the LaAlO₃ MSM PDs with three different crystal planes (100), (110), and (111).

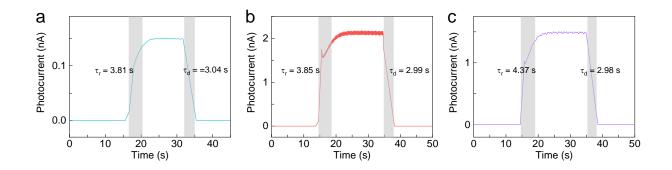


Figure S4. Iphoto-t characteristics of different crystal planes (a) (100), (b) (110), and (c) (111).